

FAST SWITCHING SURFACE MOUNT DIODES

VOLTAGE - 100Volts
POWER - 50 mW

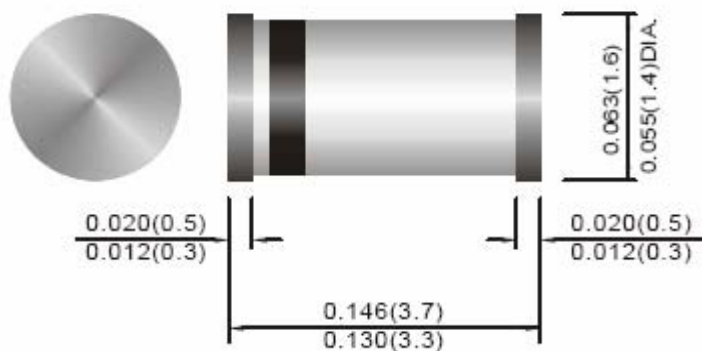
FEATURES

- Fast Switching Speed
- Surface Mount Package Ideally Suited for Automatic Insertion
- Silicon Epitaxial Planar Construction
- Lead free in comply with EU RoHS 2002/95/EC directives

MECHANICAL DATA

- Case: MINI MELF
- Terminals: Solderable per MIL-STD-750, Method 2026
- Polarity: Cathode Band
- Marking: Cathode Band Only
- Weight: 0.03 grams (approx)

MINI MELF(LL-34)



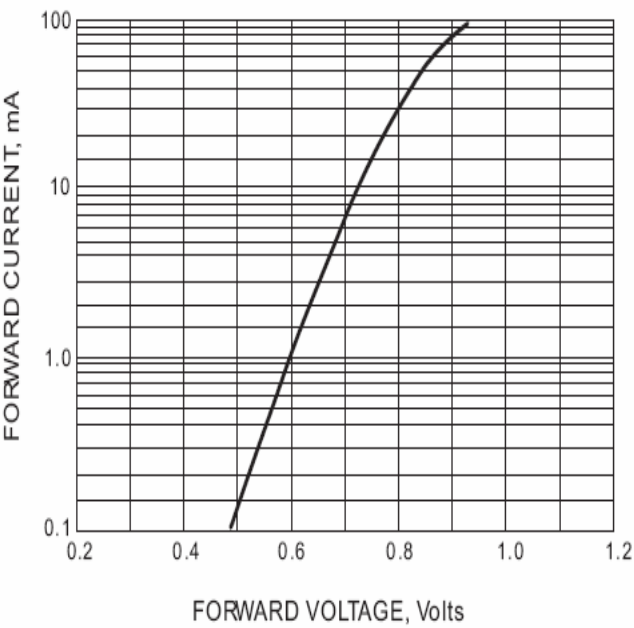
Unit :inch(mm)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS (T_J=25°C unless otherwise noted)

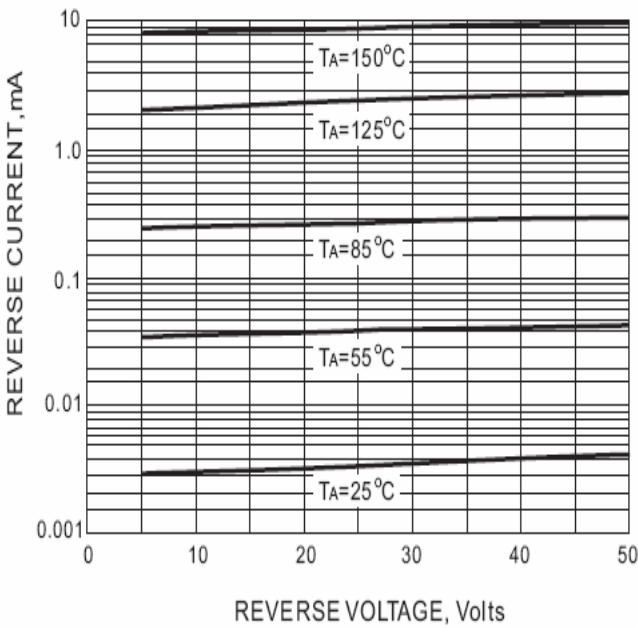
Parameter	Symbol	LL4448	Units
Peak Reverse Voltage	V _{RM}	100	V
Maximum DC Blocking Voltage	V _{bc}	75	V
Maximum Average Forward Current at T _A =25°C And f ≥ 50Hz	I _{F(AV)}	150	mA
Surge Forward Current at t ≤ 1s and T _J =25°C	I _{FSM}	500	mA
Power Dissipation at T _A =25°C	P _{tot}	500	mW
Maximum Forward Voltage at I _F =100mA	V _F	1	V
Maximum Leakage Current @V _R =20V	I _R	25	nA
@V _R =20V, T _J =150°C	I _R	50	uA
Maximum Capacitance at V _F =V _R =0	C _J	4	pF
Maximum Reverse Recovery Time From I _F =-I _R =10mA to I _{RR} =-1mA, V _R =6V R _L =100 Ω	t _{rr}	4	ns
Typical Maximum Thermal Resistance	R _{θJA}	350	°C/W
Junction Temperature	T _J	-65to+175	°C
Storage Temperature Range	T _{STG}	-65to+175	°C

NOTE:

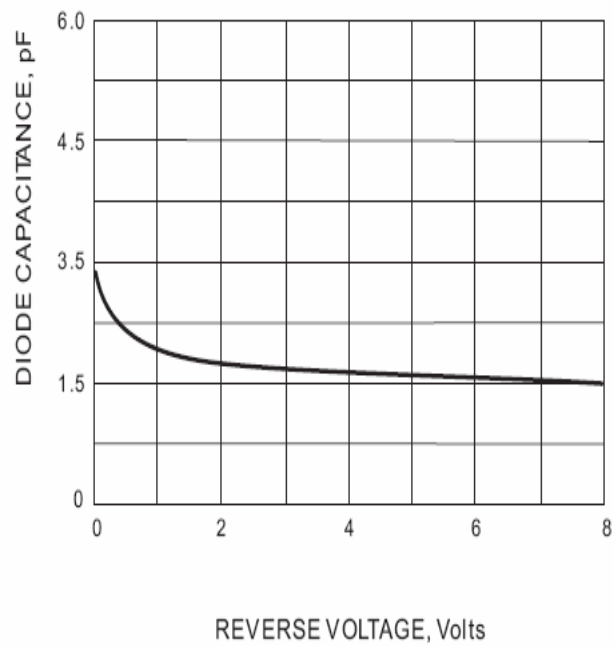
- 1.C_J at V_R=0, f=1MHz
- 2.From I_F=10mA to I_R=1mA, V_R=6Volts, R_L=100Ω



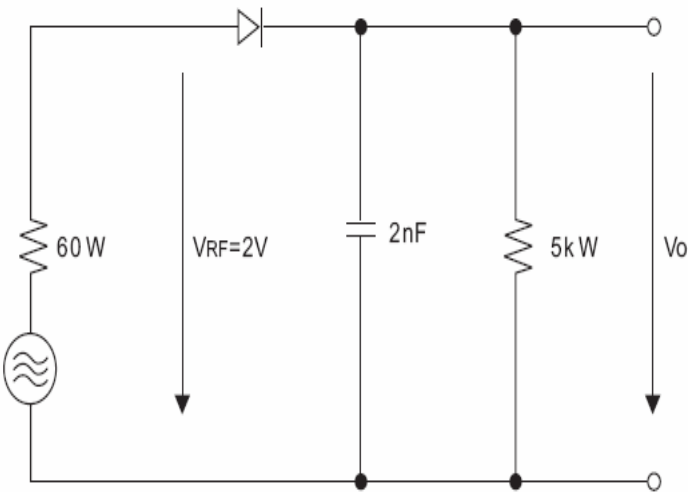
FORWARD VOLTAGE



LEAKAGE CURRENT



TYPICAL CAPATICANCE



RECTIFICATION EFFCIENCY MEASUREMENT CIRCUIT